Dual 2-Input NAND Gate

The NL27WZ00 is a high performance dual 2-input NAND Gate operating from a 2.3 V to 5.5 V supply.

- Extremely High Speed: tpp 2.4 ns (typical) at $V_{CC} = 5 \text{ V}$
- Designed for 2.3 V to 5.5 V VCC Operation
- Over Voltage Tolerant Inputs
- LVTTL Compatible Interface Capability With 5 V TTL Logic with $V_{CC} = 3 \text{ V}$
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Replacement for NC7WZ00
- Chip Complexity: FET = 112

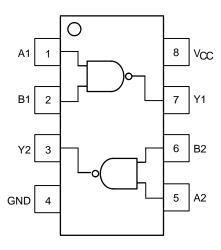


Figure 1. Pinout

PIN ASSIGNMENT

Pin	Function
1	A1
2	B1
3	Y2
4	GND
5	A2
6	B2
7	Y1
8	Vcc



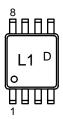
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MARKING DIAGRAM



US8 US SUFFIX CASE 493-01



D = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

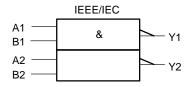


Figure 2. Logic Symbol

FUNCTION TABLE $Y = \overline{AB}$

Inp	Output	
A B		Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

H = HIGH Logic Level L = LOW Logic Level

MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
VCC	DC Supply Voltage		-0.5 to +7.0	V
٧ _I	DC Input Voltage		-0.5 to +7.0	V
٧o	DC Output Voltage		-0.5 to +7.0	V
l _{IK}	DC Input Diode Current	V _I < GND	-50	mA
lok	DC Output Diode Current	V _O < GND	-50	mA
lo	DC Output Sink Current	±50	mA	
ICC	DC Supply Current per Supply Pin		±100	mA
IGND	DC Ground Current per Ground Pin		±100	mA
TSTG	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
θ JA	Thermal Resistance	(Note 1)	250	°C/W
PD	Power Dissipation in Still Air at 85°C	;	250	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
VESD	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
I _{Latch} -Up	Latch-Up Performance	Above V _{CC} and Below GND at 85°C (Note 5)	±500	mA

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- Tested to EIA/JESD22-A114-A.
 Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
Vcc	Supply Voltage	Operating Data Retention Only	2.3 1.5	5.5 5.5	V
VI	Input Voltage	(Note 6)	0	5.5	V
VO	Output Voltage	(HIGH or LOW State)	0	Vcc	V
TA	Operating Free–Air Temperature		-40	+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$ $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0 0	20 10 5	ns/V

^{6.} Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS

			VCC	ΤΔ	$T_A = 25^{\circ}C$		-40°C ≤	T_A ≤ 85°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
٧ _{IH}	High-Level Input Voltage		2.3 to 5.5	0.7 V _{CC}			0.7 V _{CC}		V
V _{IL}	Low-Level Input Voltage		2.3 to 5.5			0.3 V _{CC}		0.3 V _{CC}	V
VOH	High-Level Output Voltage	I _{OH} = 100 μA	2.3 to 5.5	V _{CC} -0.1	VCC		V _{CC} -0.1		V
	V _{IN} = V _{IL} or V _{IL}	$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.1		1.9		
		$I_{OH} = -12 \text{ mA}$	2.7	2.2	2.4		2.2		
		$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.7		2.4		
		$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.5		2.3		
		$I_{OH} = -32 \text{ mA}$	4.5	3.8	4.0		3.8		
VOL	Low-Level Output Voltage	I _{OL} = 100 μA	2.3 to 5.5			0.1		0.1	V
	$V_{IN} = V_{IH}$	I _{OL} = 8 mA	2.3		0.20	0.3		0.3	
		I _{OL} = 12 mA	2.7		0.22	0.4		0.4	
		I _{OL} = 16 mA	3.0		0.28	0.4		0.4	
		I _{OL} = 24 mA	3.0		0.38	0.55		0.55	
		I _{OL} = 32 mA	4.5		0.42	0.55		0.55	
I _{IN}	Input Leakage Current	$V_{IN} = V_{CC}$ or GND	0 to 5.5			±0.1		±1.0	μΑ
Icc	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1		10	μΑ

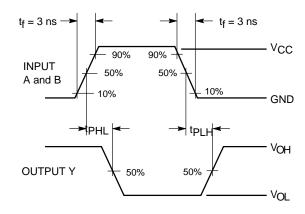
AC ELECTRICAL CHARACTERISTICS $t_R = t_F = 3.0 \text{ ns}$

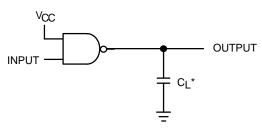
			VCC	T _A = 25°C		-40°C ≤ 7			
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
tPLH	Propagation Delay	$R_L = 1 M\Omega$, $C_L = 15 pF$	2.5 ± 0.2	1.2	3.2	5.3	1.2	5.7	ns
^t PHL	(Figure 3 and 4)	$R_L = 1 M\Omega$, $C_L = 15 pF$	3.3 ± 0.3	0.8	2.4	3.7	0.8	4.0	
		$R_L = 500 \Omega, C_L = 50 pF$		1.2	3.0	4.6	1.2	4.9	
		$R_L = 1 M\Omega$, $C_L = 15 pF$	5.0 ± 0.5	0.5	1.9	2.9	0.5	3.2	
		$R_L = 500 \Omega, C_L = 50 pF$		0.8	2.4	3.6	0.8	3.9	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 7)	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	9	pF
	(NOIE 1)	10 MHz, V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	11	1

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.





*C_L includes all probe and jig capacitances. A 1–MHz square input wave is recommended for propagation delay tests.

Figure 3. Switching Waveform

Figure 4. Test Circuit

DEVICE ORDERING INFORMATION

			Device No	menclature				
Device Order Number	Logic Circuit Indicator	No. of Gates per Package	Temp Range Identifier	Technology	Device Function	Package Suffix	Package Type	Tape and Reel Size
NL27WZ00US	NL	2	7	WZ	00	US	US8	178 mm, 3000 Unit

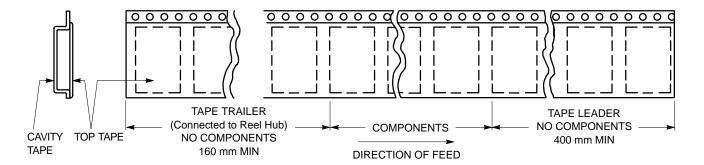


Figure 5. Tape Ends for Finished Goods

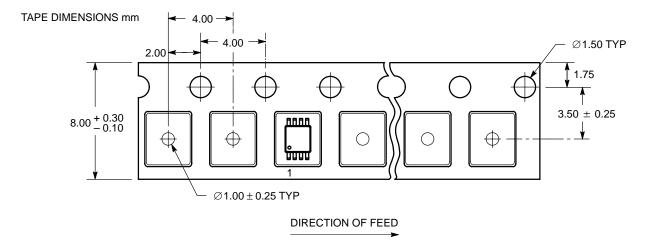


Figure 6. US8 Reel Configuration/Orientation

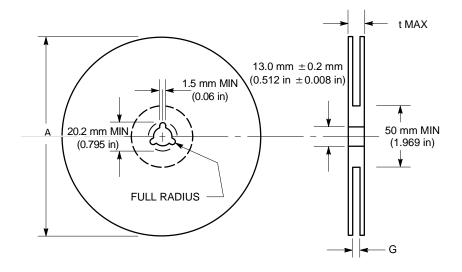


Figure 7. Reel Dimensions

REEL DIMENSIONS

Tape Size	T and R Suffix	A Max	G	t Max
8 mm	US	178 mm (7 in)	8.4 mm, + 1.5 mm, -0.0 (0.33 in + 0.059 in, -0.00)	14.4 mm (0.56 in)

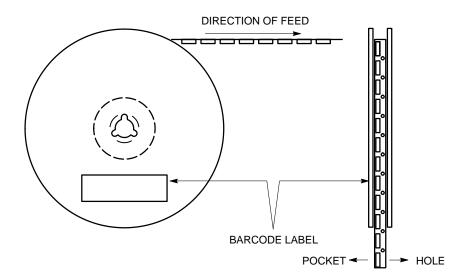
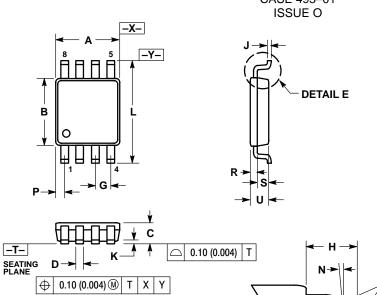


Figure 8. Reel Winding Direction

PACKAGE DIMENSIONS

US8 **US SUFFIX** CASE 493-01



R 0.10 TYP

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETERS

 3. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055") PER SIDE.

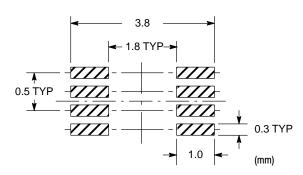
 4. DIMENSION "B" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSION. INTER-LEAD FLASH AND PROTRUSION SHALL NOT E3XCEED 0.140 (0.0055") PER SIDE.

 5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076-0.0203 MM. (300-800 INCH).

- INCH).

 6. ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002").

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.90	2.10	0.075	0.083	
В	2.20	2.40	0.087	0.094	
С	0.60	0.90	0.024	0.035	
D	0.17	0.25	0.007	0.010	
F	0.20	0.35	0.008	0.014	
G	0.50	BSC	0.020	BSC	
Н	0.40	REF	0.016 REF		
J	0.10	0.18	0.004	0.007	
K	0.00	0.10	0.000	0.004	
L	3.00	3.20	0.118	0.126	
M	0 °	6 °	0 °	6 °	
N	5°	10 °	5 °	10 °	
P	0.28	0.44	0.011	0.017	
R	0.23	0.33	0.009	0.013	
S	0.37	0.47	0.015	0.019	
U	0.60	0.80	0.024	0.031	
٧	0.12	BSC	0.00	BSC	



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